

**Atty. Docket No.**

**Serial No.**

INFORMATION DISCLOSURE  
CITATION

**160-386**

**10/609,410**

**Applicant**

NAKAMURA et al.

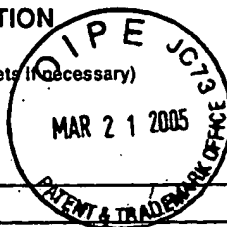
Filing Date

**TC/A.U.**

**July 1, 2003**

2825

(Use several sheets if necessary)



## U.S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS						TRANSLATION	
DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO	
✓ 62-2675	01/1987	JAPAN					
✓ 83103775	04/1994	TAIWAN					
✓ 10-0225612	07/1999	KOREA					

**OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)**

✓✓	AKASAKI et al., "MOVPE Growth of GaN and Al <sub>x</sub> Ga <sub>1-x</sub> N and Their Luminescence and Electrical Properties," Memoirs of the Faculty of Engineering, Nagoya Univ., Vol. 43, No. 2 (1991)
✓✓	Williams Modern GaAs Processing Method (1990), p. 219
✓✓	Database WPI, Week 9444, Derwent Publications Ltd., London, Nichia Kagaku Kogyo KK (see Abstract)
✓✓	JP 6275868 (09/30/1994) (see Abstract)
✓✓	Written Opposition dated January 15, 2001, p. 1-3
✓✓	Written Opposition dated January 19, 2001, pp. 1-5

**\*Examiner**

**Date Considered**

08/10/05

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

07/01/03

10/609,410

INFORMATION DISCLOSURE  
CITATION

ATTY. DOCKET NO.

DIVISIONAL OF SERIAL NO.

160-386

10/292,583

APPLICANT

NAKAMURA et al

(Use several sheets if necessary)

FILING DATE

GROUP

July 1, 2003

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
VY	03-218625	9/1991	Japan			abs
↑	05-013812	1/1993	Japan			abs
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	61-144659	9/1986	Japan			abs
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\*Examiner

Date Considered

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		160-386	10/292,583
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		NAKAMURA et al	
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✓	2-68968	3/90	Japan
✓	5-13816	1/93	Japan

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✓	Hayes et al Proceedings of Symposium B 1990 Extended Abstracts EA-21 Electronic Optical and Device Properties of Layered Structures
✓	Amano et al Japanese Journal of Applied Physics Vol. 28 No. 12, 1989 L2112-L2114 P-Type Conduction in Mg-Doped GaN Treated with Low-Energy Electron Beam Irradiation (LEEBI)
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✓	Su et al Jpn. J. Applied Physics Vol. 30 No. 5, May 1991 914-916 Ohmic Contacts AuGeNi etc.
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✓	Foresi et al "Metal contacts to gallium nitride" Appl. Phys. Letts 62 (1993) 31 May No. 22, pp. 2859-2861
✓	Akasaki et al "High efficiency UV..." Proc. of the SPIE, Phys. Concepts of Materials...28 Oct. 1990, Aachen, DE, pp 138-149
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✓	Database WPI, Week 9444, Derwent Publications Ltd. London, GB AN 94-352820 & JP A-6 275 868 (Nichia Kagaku Kogyo KK) 20 Sept. 1994, see abstract
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*Examiner	V. Yeastman	Date Considered	04/26/05
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